

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please cancel claims 52-61 and 63, and amend claim 38, as follows:

Listing of Claims:

1-37. (Cancelled)

38. (Currently Amended) An in-process substrate structure including a plurality of contact regions and a plurality of non-contact regions adjacent the contact regions on a surface of the substrate, the in-process substrate structure comprising:

a selectively formed single crystal contact on each contact region, each single crystal contact being isolated from single crystal contacts on adjacent contact regions, each single crystal contact having an arcuate, convex upper surface intersected by two sidewall surfaces, the two sidewall surfaces being substantially perpendicular to the surface of the substrate, each of the two sidewall surfaces do not abut another surface.

39-44. (Cancelled)

45. (Previously presented) The substrate of claim 38 wherein the non-contact regions adjacent to the contact region comprise isolation oxide regions.

46. (Previously presented) The substrate of claim 38 wherein the substrate comprises silicon.

47. (Previously presented) The substrate of claim 38 wherein the substrate comprises gallium arsenide.

48. (Previously presented) The substrate of claim 38 wherein the substrate comprises silicon germanium.

49. (Previously Presented) The substrate of claim 38 wherein the single crystal contact comprises silicon.

50. (Previously Presented) The substrate of claim 38 wherein the single crystal contact comprises gallium arsenide.

51. (Previously Presented) The substrate of claim 38 wherein the single crystal contact comprises silicon germanium.

52.-61. (Cancelled)

62. (Previously Presented) The in-process semiconductor of claim 38 wherein the selectively formed single crystal contact extends past the contact region and over only a peripheral region of one of the adjacent non-contact regions.

63. (Canceled)